

Cool MOS™ Power Transistor

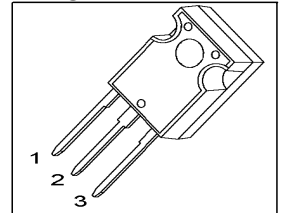
Feature

- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- Ultra low effective capacitances
- Improved noise immunity

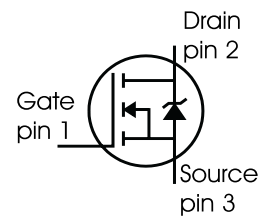
Product Summary

V_{DS}	600	V
$R_{DS(on)}$	0.38	Ω
I_D	11	A

P-TO247



Type	Package	Ordering Code	Marking
SPW11N60C2	P-TO247	Q67040-S4313	11N60C2



Maximum Ratings, at $T_C = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	I_D	11	A
$T_C = 25^\circ\text{C}$		7	
$T_C = 100^\circ\text{C}$			
Pulsed drain current, t_p limited by T_{jmax}	$I_{D\text{ pulsed}}$	22	
Avalanche energy, single pulse	E_{AS}	340	mJ
$I_D=5.5\text{A}$, $V_{DD}=50\text{V}$			
Avalanche energy, repetitive t_{AR} limited by $T_{jmax}^{1)}$	E_{AR}	0.6	
$I_D=11\text{A}$, $V_{DD}=50\text{V}$			
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	11	A
Reverse diode dv/dt	dv/dt	6	V/ns
$I_S=11\text{A}$, $V_{DS} < V_{DD}$, di/dt=100A/ μs , $T_{jmax}=150^\circ\text{C}$			
Gate source voltage	V_{GS}	± 20	V
Power dissipation, $T_C = 25^\circ\text{C}$	P_{tot}	125	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	1	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
Linear derating factor		-	-	1	W/K
Soldering temperature, 1.6 mm (0.063 in.) from case for 10s	T_{sold}	-	-	260	°C

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Static Characteristics

Drain-source breakdown voltage $V_{GS}=0V, I_D=0.25mA$	$V_{(BR)DSS}$	600	-	-	V
Drain-source avalanche breakdown voltage $V_{GS}=0V, I_D=11A$	$V_{(BR)DS}$	-	700	-	
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=0.5mA$	$V_{GS(th)}$	3.5	4.5	5.5	
Zero gate voltage drain current $V_{DS} = 600V, V_{GS} = 0V, T_j = 25\text{ °C}$ $V_{DS} = 600V, V_{GS} = 0V, T_j = 150\text{ °C}$	I_{DSS}	-	-	25 250	μA
Gate-source leakage current $V_{GS}=20V, V_{DS}=0V$	I_{GSS}	-	-	100	
Drain-source on-state resistance $V_{GS}=10V, I_D=7A, T_j=25\text{ °C}$	$R_{DS(on)}$	-	0.34	0.38	Ω
Gate input resistance $f = 1\text{ MHz, open drain}$	R_G	-	0.86	-	

¹Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$.

Electrical Characteristics , at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Characteristics						
Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(ON)max}$ $I_D = 7A$	3	6	-	S
Input capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V,$ $f = 1MHz$	-	1460	-	pF
Output capacitance	C_{oss}		-	610	-	
Reverse transfer capacitance	C_{rss}		-	21	-	
Effective output capacitance, ¹⁾ energy related	$C_{o(er)}$	$V_{GS} = 0V,$ $V_{DS} = 0V$ to 480V	-	45	-	pF
Effective output capacitance, ²⁾ time related	$C_{o(tr)}$		-	85	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 380V, V_{GS} = 0/13V,$ $I_D = 11A, R_G = 6.8\Omega,$ $T_j = 125^{\circ}C$	-	13	-	ns
Rise time	t_r		-	40	-	
Turn-off delay time	$t_{d(off)}$		-	48	72	
Fall time	t_f		-	9	13.5	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 350\text{V}$, $I_D = 11\text{A}$	-	10.5	-	nC
Gate to drain charge	Q_{gd}		-	24	-	
Gate charge total	Q_g	$V_{DD} = 350\text{V}$, $I_D = 11\text{A}$, $V_{GS} = 0$ to 10V	-	41.5	54	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 350\text{V}$, $I_D = 11\text{A}$	-	8	-	V

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

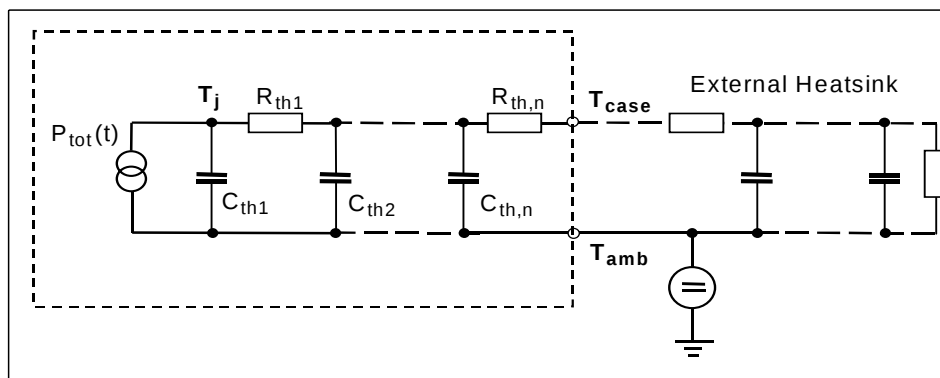
²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Electrical Characteristics, at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Characteristics						
Inverse diode continuous forward current	I_S	$T_C=25^{\circ}\text{C}$	-	-	11	A
Inverse diode direct current, pulsed	I_{SM}		-	-	22	
Inverse diode forward voltage	V_{SD}	$V_{GS}=0\text{V}$, $I_F=I_S$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R=350\text{V}$, $I_F=I_S$, $di_F/dt=100\text{A}/\mu\text{s}$	-	650	1105	ns
Reverse recovery charge	Q_{rr}		-	7.9	-	μC
Peak reverse recovery current	I_{rrm}		-	30	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt		-	600	-	$\text{A}/\mu\text{s}$

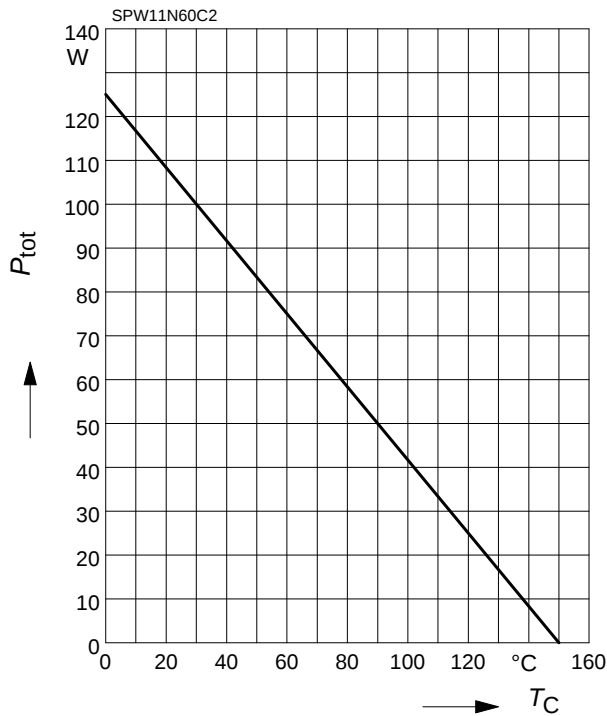
Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
R_{th1}	0.015	K/W	C_{th1}	0.0002121	Ws/K
R_{th2}	0.034		C_{th2}	0.0007091	
R_{th3}	0.042		C_{th3}	0.001184	
R_{th4}	0.116		C_{th4}	0.001527	
R_{th5}	0.149		C_{th5}	0.011	
R_{th6}	0.059		C_{th6}	0.089	



1 Power dissipation

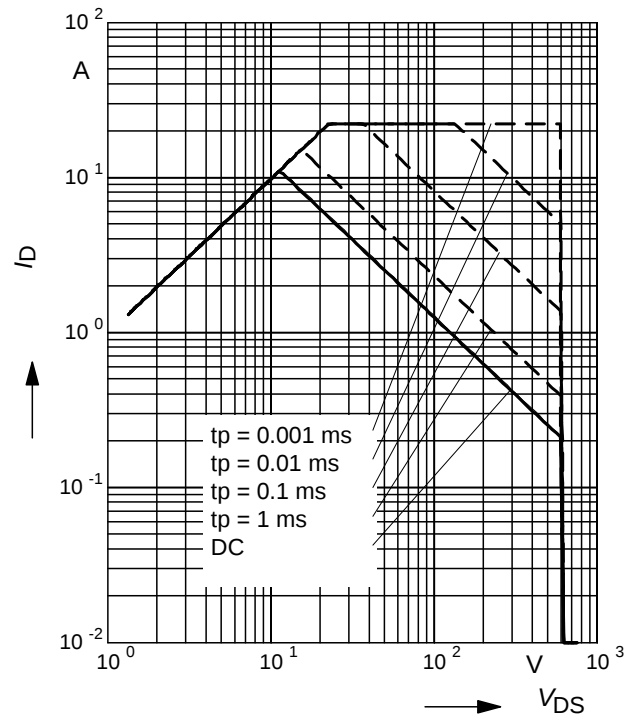
$$P_{\text{tot}} = f(T_C)$$



2 Safe operating area

$$I_D = f(V_{DS})$$

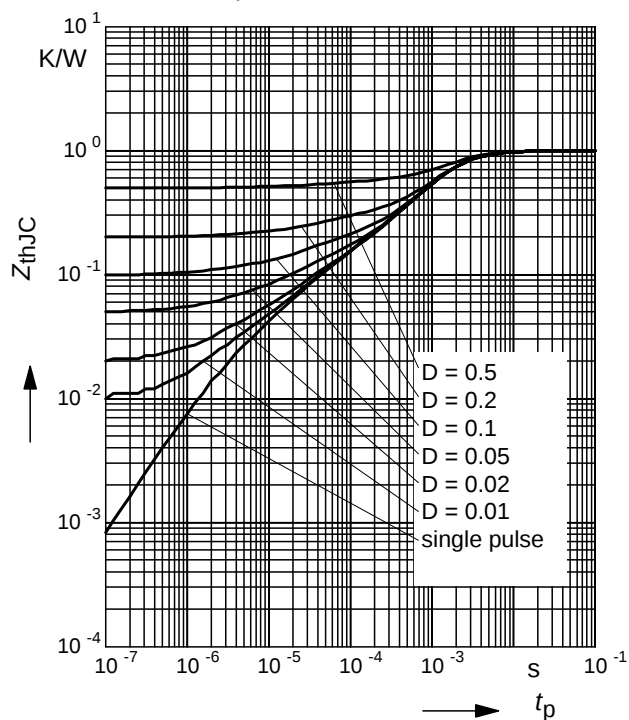
parameter : $D = 0$, $T_C = 25^\circ\text{C}$



3 Transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

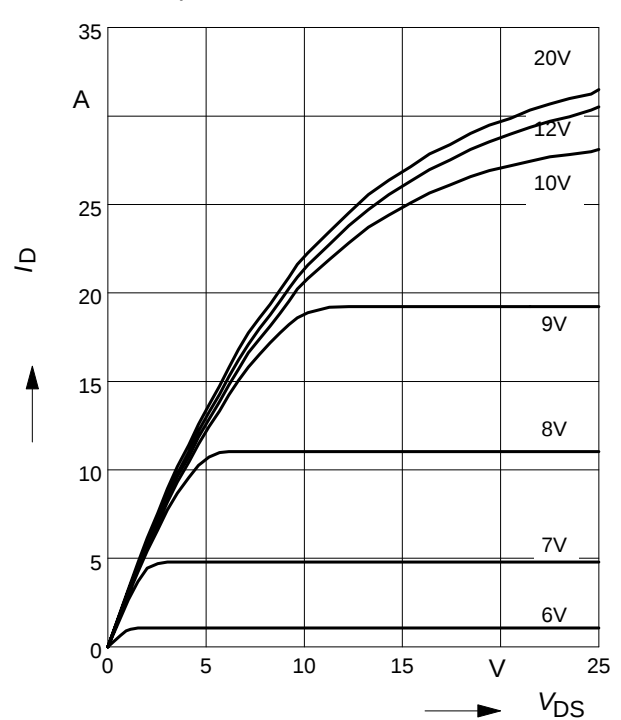
parameter: $D = t_p/T$



4 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

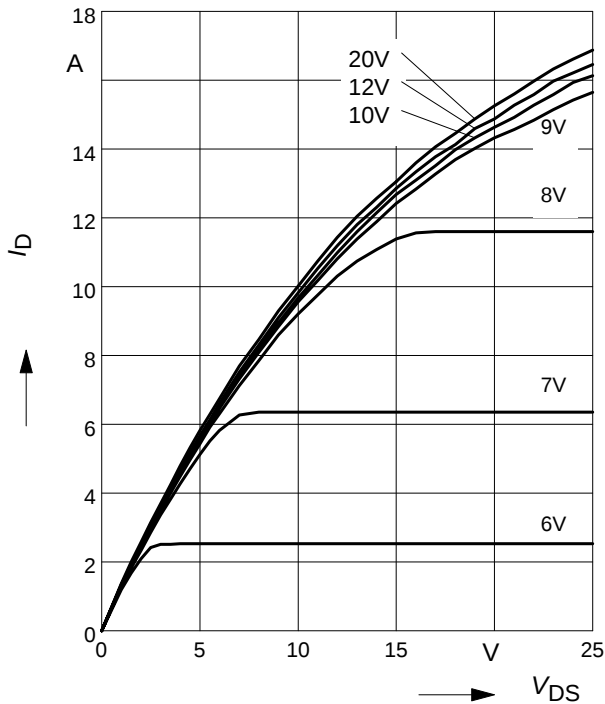
parameter: $t_p = 10 \mu\text{s}$, V_{GS}



5 Typ. output characteristic

$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$

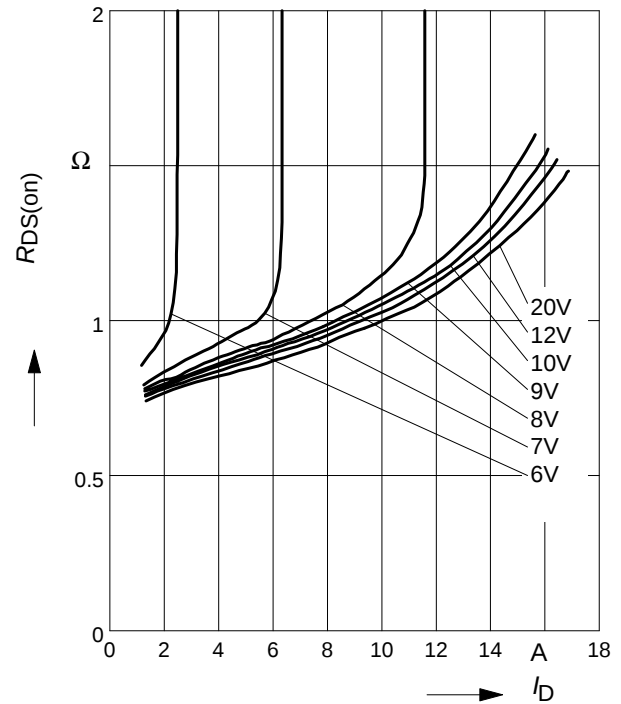
parameter: $t_p = 10 \mu\text{s}$, V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$

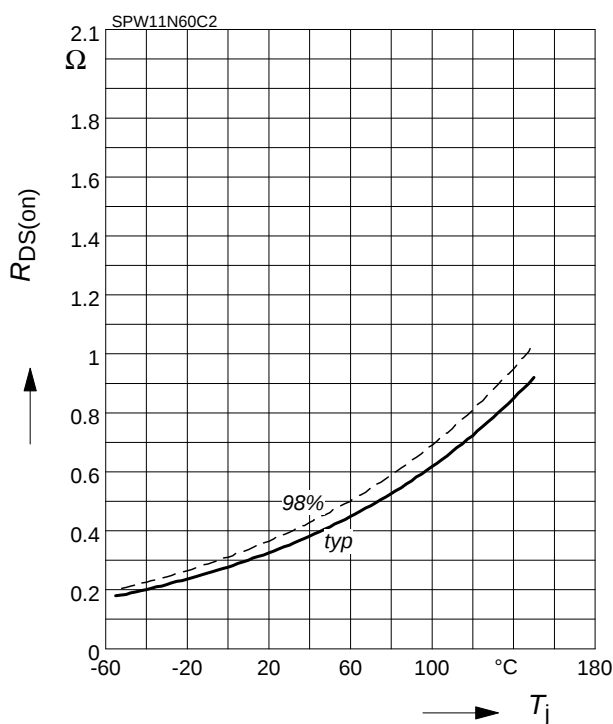
parameter: $T_j = 150^\circ\text{C}$, V_{GS}



7 Drain-source on-state resistance

$R_{DS(on)} = f(T_j)$

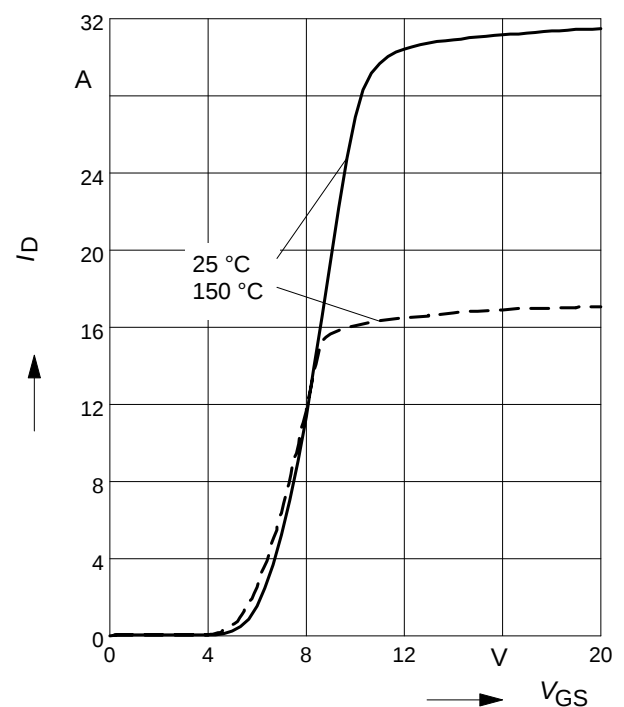
parameter: $I_D = 7 \text{ A}$, $V_{GS} = 10 \text{ V}$



8 Typ. transfer characteristics

$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

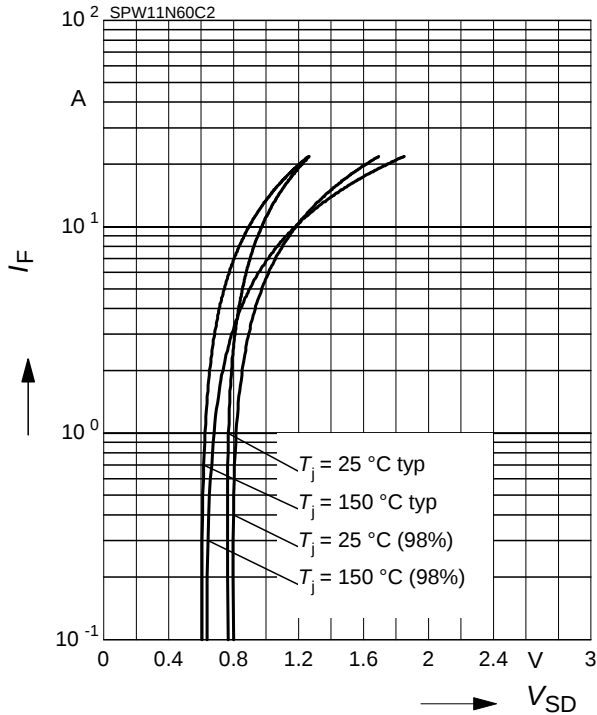
parameter: $t_p = 10 \mu\text{s}$



9 Forward characteristics of body diode

$$I_F = f(V_{SD})$$

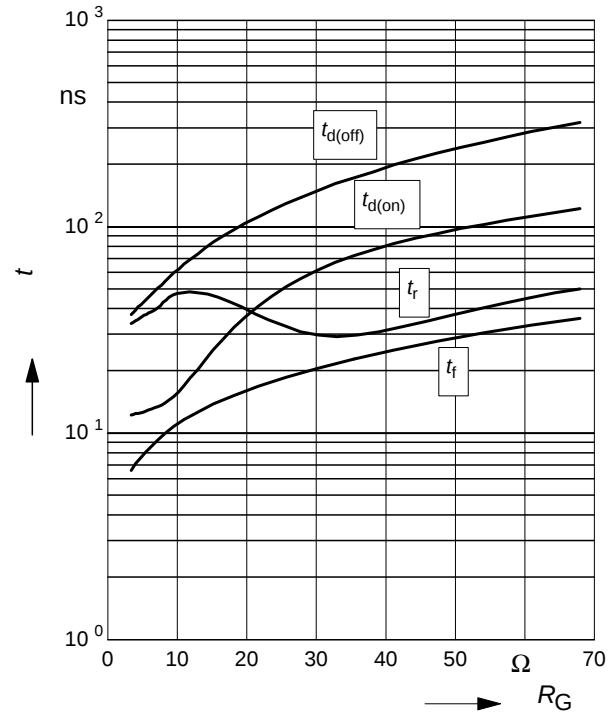
parameter: T_j , $t_p = 10 \mu s$



10 Typ. switching time

$$t = f(R_G), \text{ inductive load, } T_j = 125 \text{ °C}$$

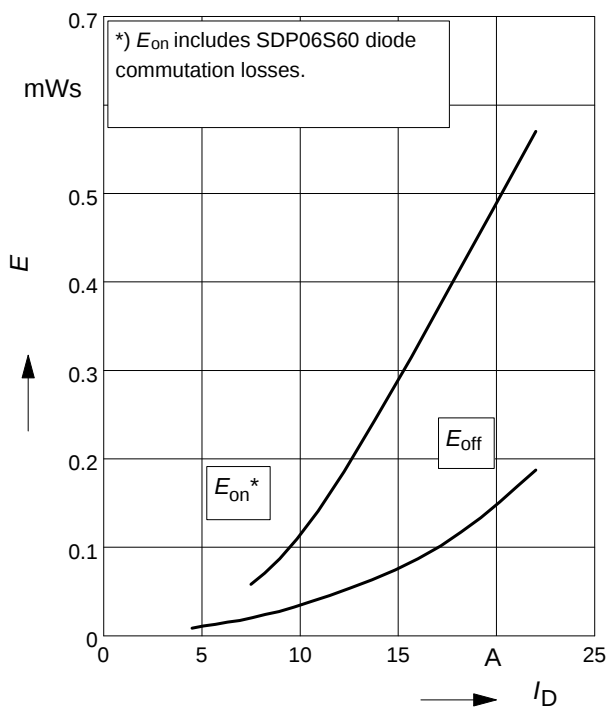
par.: $V_{DS} = 380 \text{ V}$, $V_{GS} = 0/+13 \text{ V}$, $I_D = 11 \text{ A}$



11 Typ. switching losses

$$E = f(I_D), \text{ inductive load, } T_j = 125 \text{ °C}$$

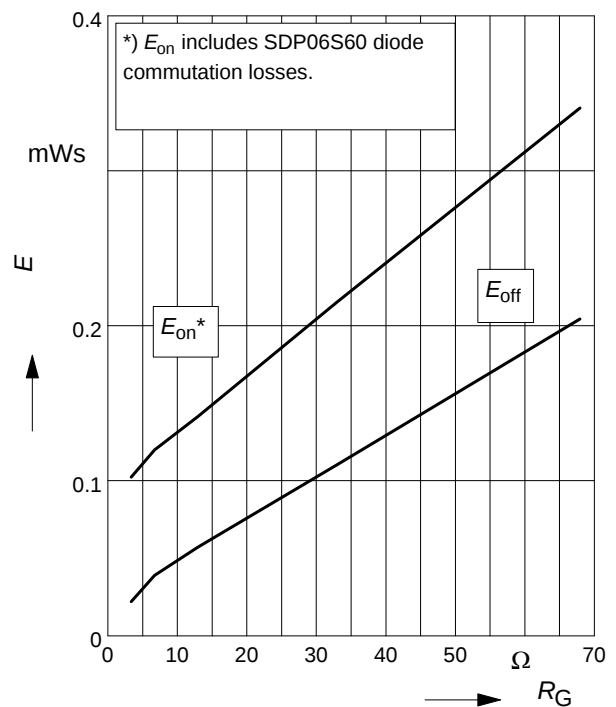
par.: $V_{DS} = 380 \text{ V}$, $V_{GS} = 0/+13 \text{ V}$, $R_G = 6.8 \Omega$



12 Typ. switching losses

$$E = f(R_G), \text{ inductive load, } T_j = 125 \text{ °C}$$

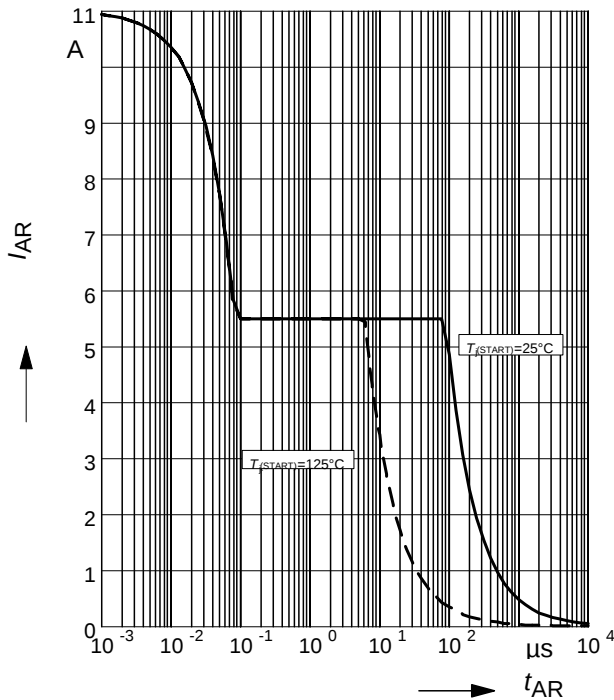
par.: $V_{DS} = 380 \text{ V}$, $V_{GS} = 0/+13 \text{ V}$, $I_D = 11 \text{ A}$



13 Avalanche SOA

$$I_{AR} = f(t_{AR})$$

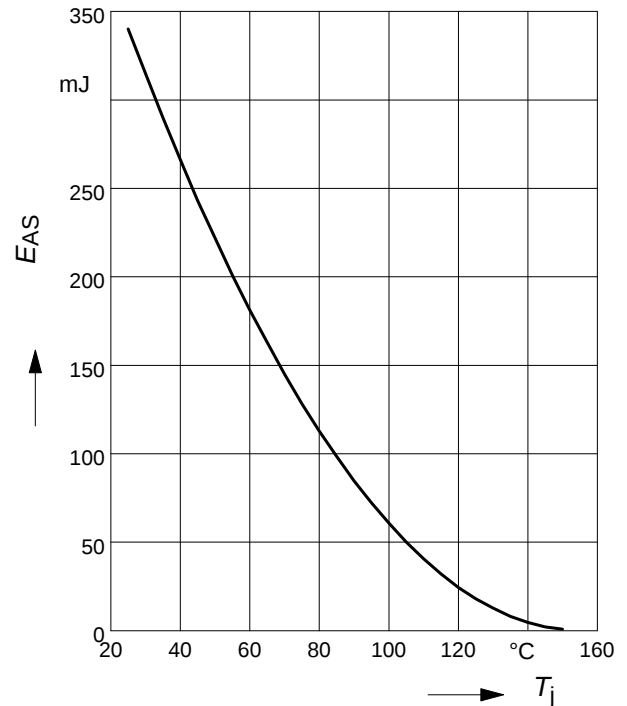
par.: $T_j \leq 150^\circ\text{C}$



14 Avalanche energy

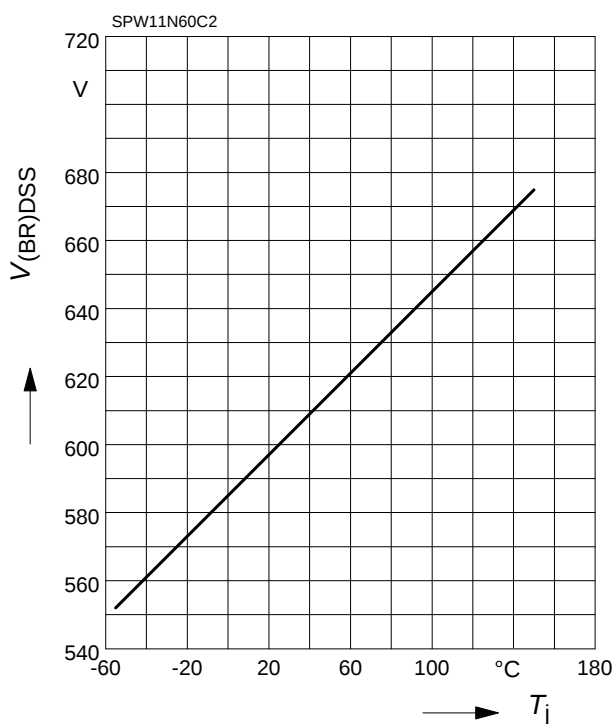
$$E_{AS} = f(T_j)$$

par.: $I_D = 5.5\text{ A}$, $V_{DD} = 50\text{ V}$



15 Drain-source breakdown voltage

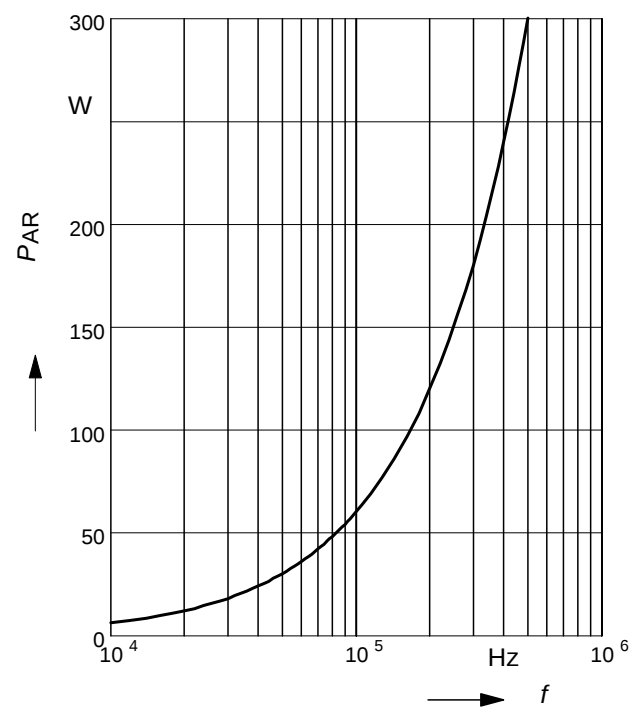
$$V_{(BR)DSS} = f(T_j)$$



16 Avalanche power losses

$$P_{AR} = f(f)$$

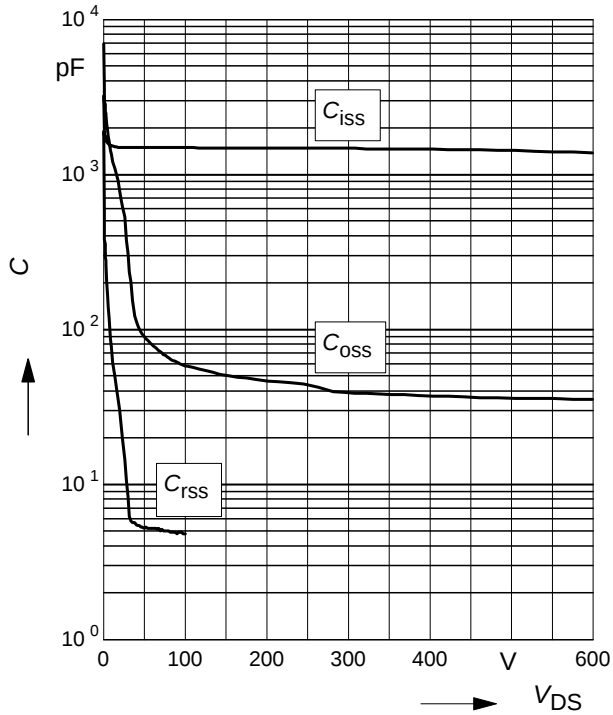
parameter: $E_{AR} = 0.6\text{ mJ}$



17 Typ. capacitances

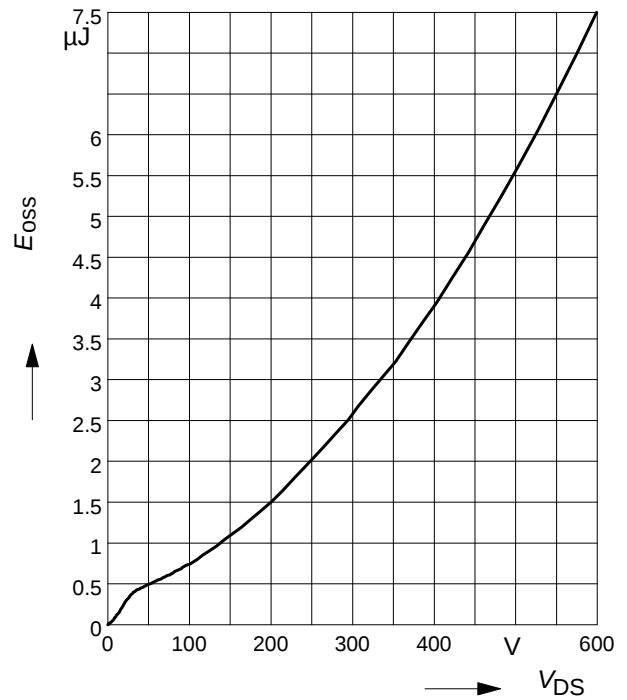
$$C = f(V_{DS})$$

parameter: $V_{GS}=0V$, $f=1\text{ MHz}$

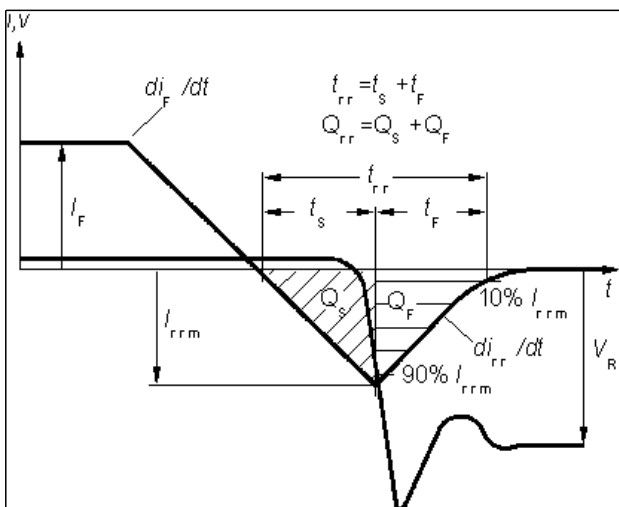


18 Typ. C_{OSS} stored energy

$$E_{OSS}=f(V_{DS})$$



Definition of diodes switching characteristics



General tolerance unless otherwise specified: Leadframe parts: ± 0.05
Package parts: ± 0.12

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